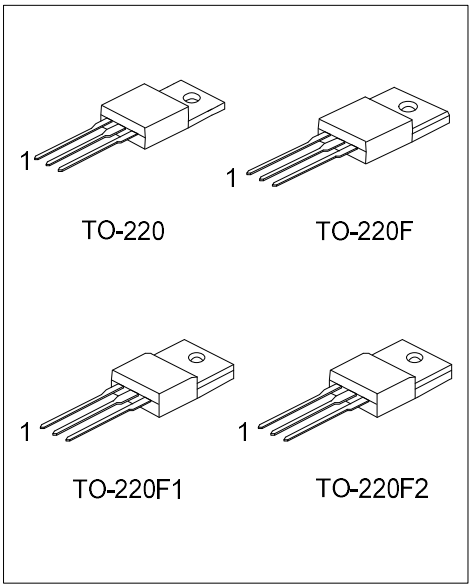
8N100-C

Power MOSFET

8.0A, 1000V N-CHANNEL POWER MOSFET



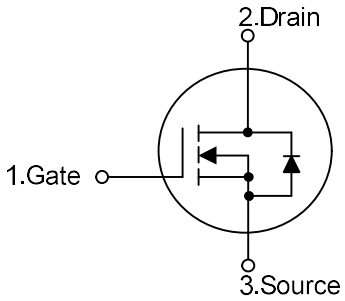
■ DESCRIPTION

The UTC **8N100-C** provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES0

* $R_{DS(ON)} \leq 1.45\ \Omega$ @ V_{GS}=10V, I_D=4.0A
* Low Reverse Transfer Capacitance
* Fast Switching Capability
* Avalanche Energy Specified
* Improved dv/dt Capability, High Ruggedness

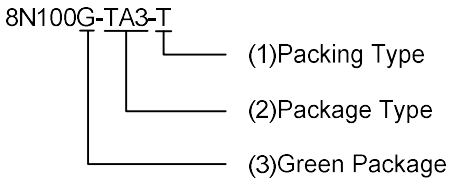
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8N100L-TA3-T	8N100G-TA3-T	TO-220	G	D	S	Tube
8N100L-TF1-T	8N100G-TF1-T	TO-220F1	G	D	S	Tube
8N100L-TF2-T	8N100G-TF2-T	TO-220F2	G	D	S	Tube
8N100L-TF3-T	8N100G-TF3-T	TO-220F	G	D	S	Tube

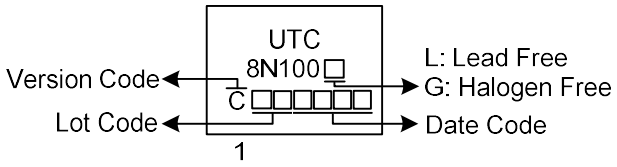
Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube
(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F
(3) G: Halogen Free and Lead Free, L: Lead Free

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■ MARKING


UTC
8N100□
C□□□□□□
Version Code
Lot Code
1
L: Lead Free
G: Halogen Free
Date Code

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	1000	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	8	A
	Pulsed (Note 2)	I_{DM}	24	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	843	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	6	V/ns
Power Dissipation	TO-220	P_D	180	W
	TO-220F/TO-220F1 TO-220F2		60	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 60mH, I_{AS} = 5.3A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 8.0A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

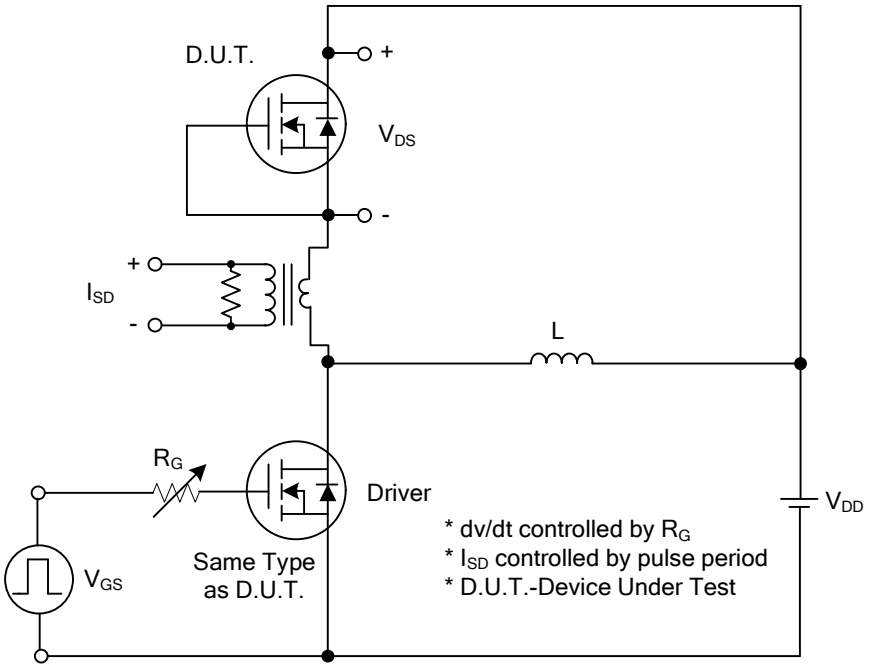
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-220	θ_{JC}	0.69	°C/W
	TO-220F/TO-220F1 TO-220F2		2.08	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

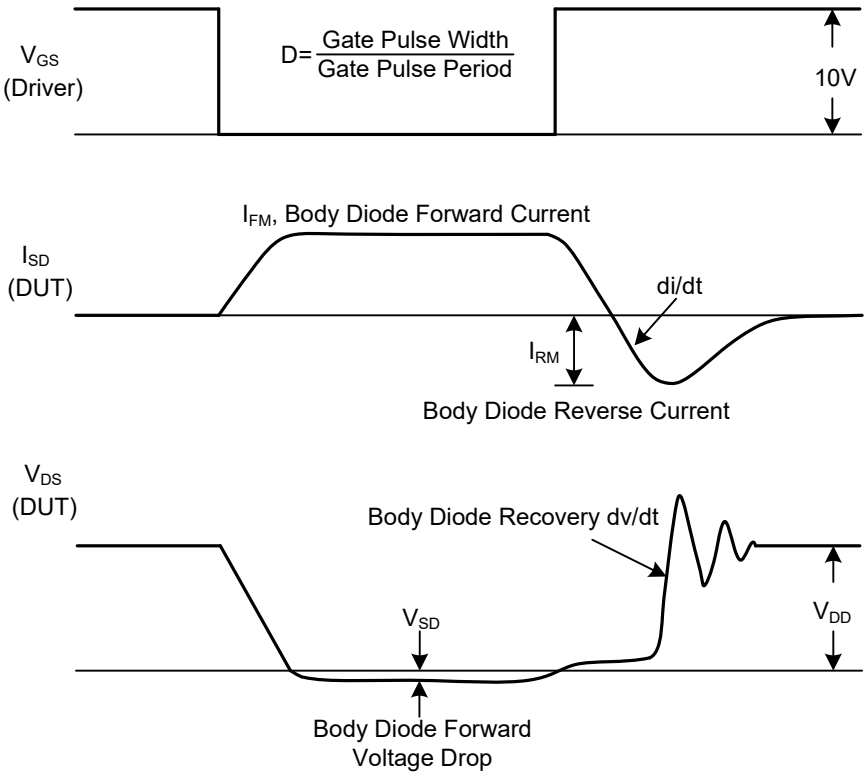
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	1000			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=1000V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	3.0		5.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=4.0A			1.45	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1MHz		2165		pF
Output Capacitance	C_{OSS}			210		pF
Reverse Transfer Capacitance	C_{RSS}			30		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	V_{DS}=300V, V_{GS}=10V, I_D=8.0A I_G=1mA (Note 1, 2)		53		nC
Gate-Source Charge	Q_{GS}			10		nC
Gate-Drain Charge	Q_{GD}			12		nC
Turn-On Delay Time (Note 1)	$t_{D(ON)}$	V_{DD}=400V, V_{GS}=10V, I_D=8.0A, R_G=25Ω (Note 1, 2)		42		ns
Turn-On Rise Time	t_R			38		ns
Turn-Off Delay Time	$t_{D(OFF)}$			194		ns
Turn-Off Fall Time	t_F			52		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				8	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				24	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I_S=8.0A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	I_S=8.0A, V_{GS}=0V, dI_F/dt=100A/μs		850		nS
Body Diode Reverse Recovery Charge	Q_{rr}			10.5		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

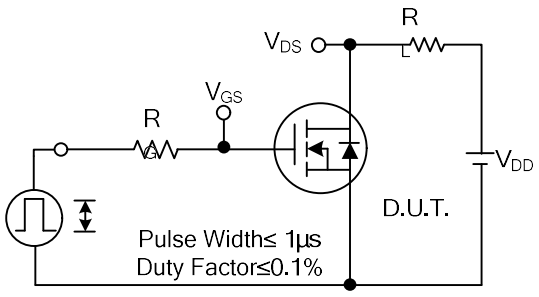


Peak Diode Recovery dv/dt Test Circuit

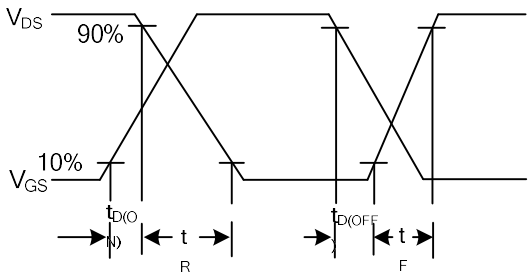


Peak Diode Recovery dv/dt Waveforms

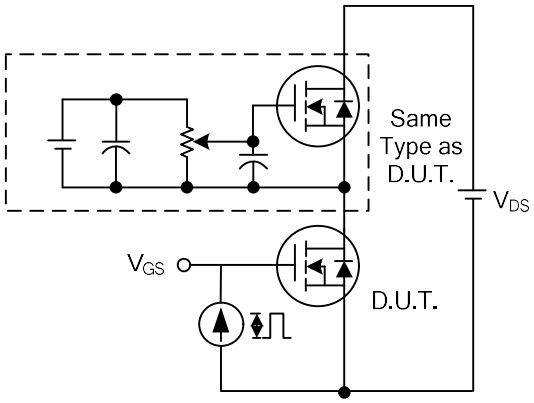
■ TEST CIRCUITS AND WAVEFORMS



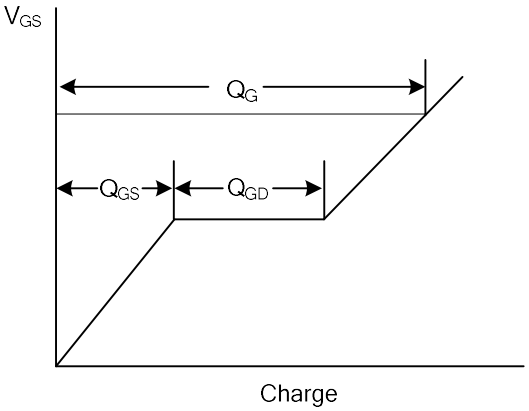
Switching Test Circuit



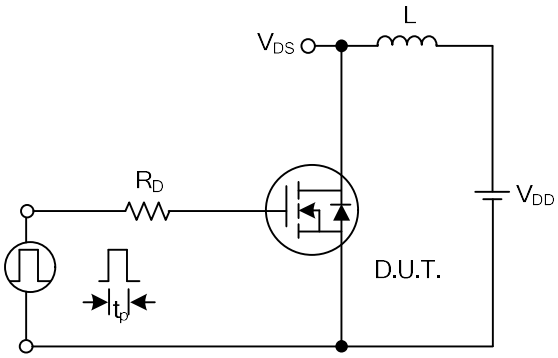
Switching Waveforms



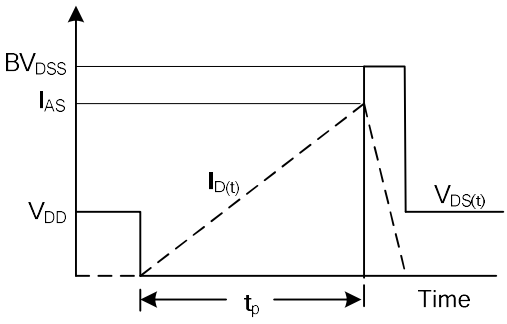
Gate Charge Test Circuit



Gate Charge Waveform



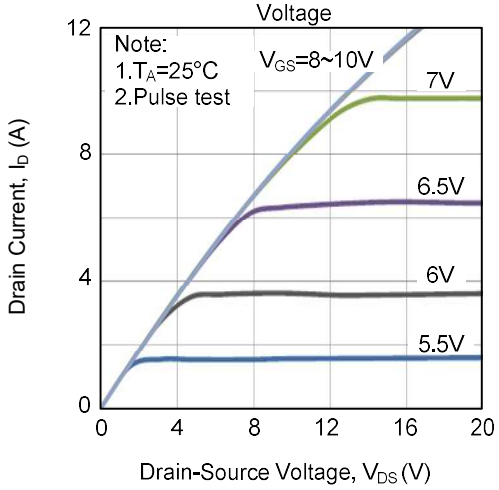
Unclamped Inductive Switching Test Circuit



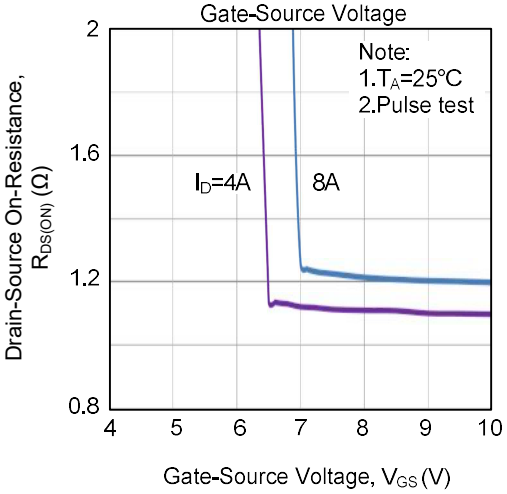
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

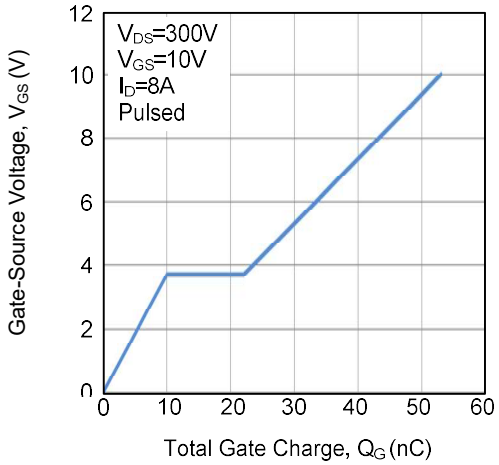
Drain Current vs. Drain-Source Voltage



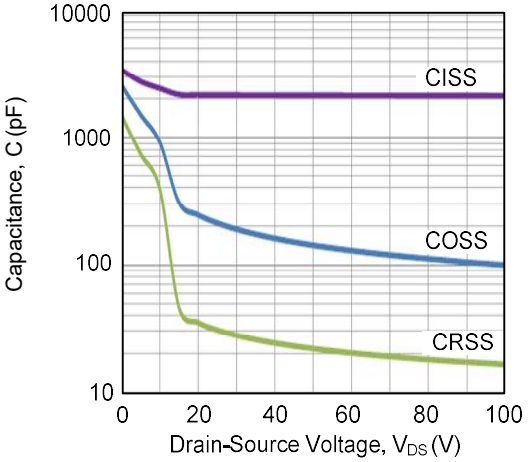
Drain-Source On-Resistance vs. Gate-Source Voltage



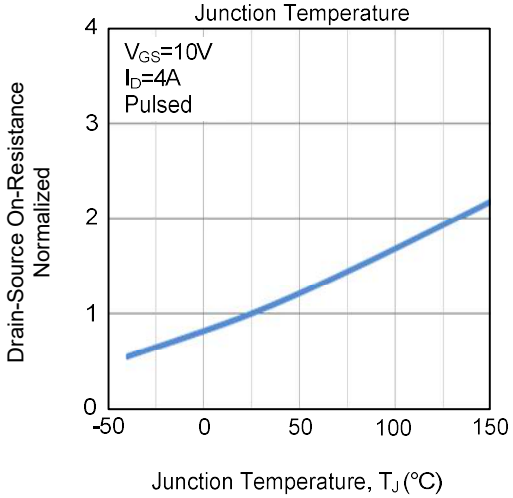
Gate Charge Characteristics



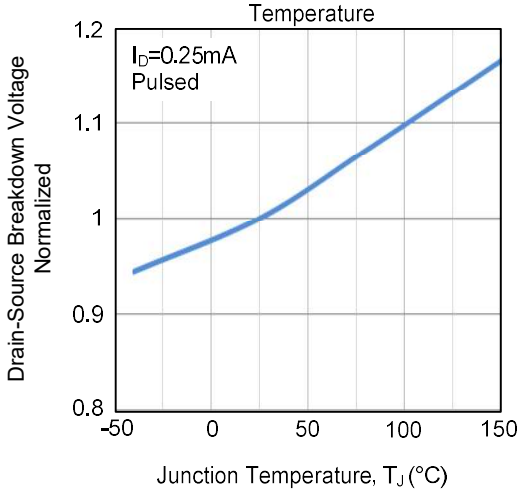
Capacitance Characteristics



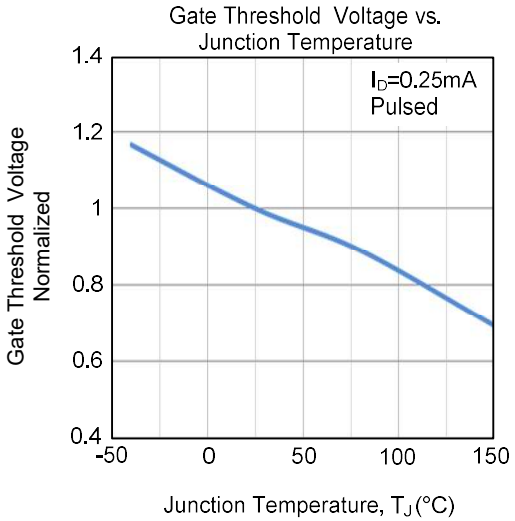
Drain-Source On-Resistance vs. Junction Temperature

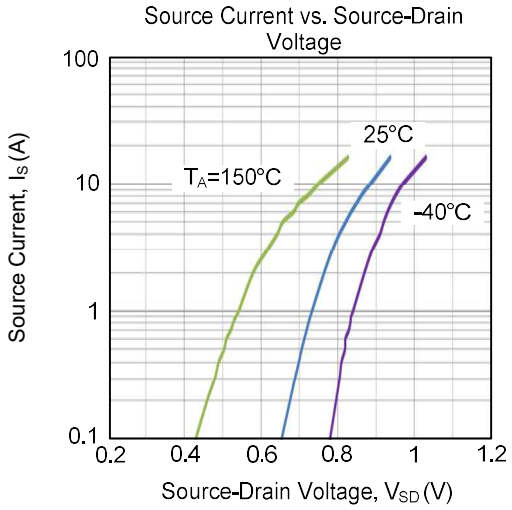


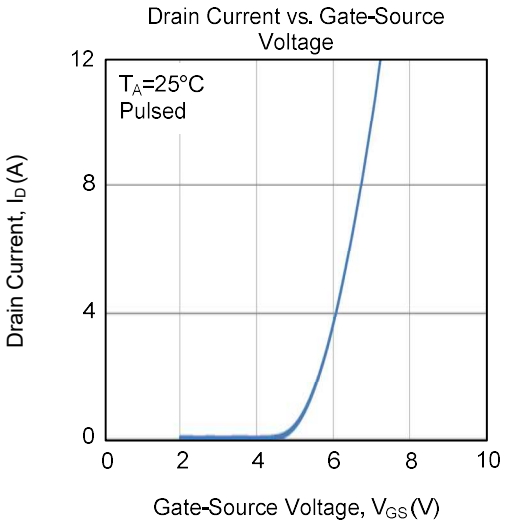
Breakdown Voltage vs. Junction Temperature

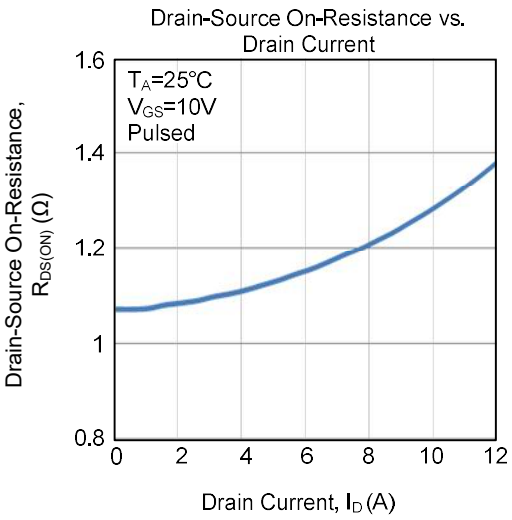


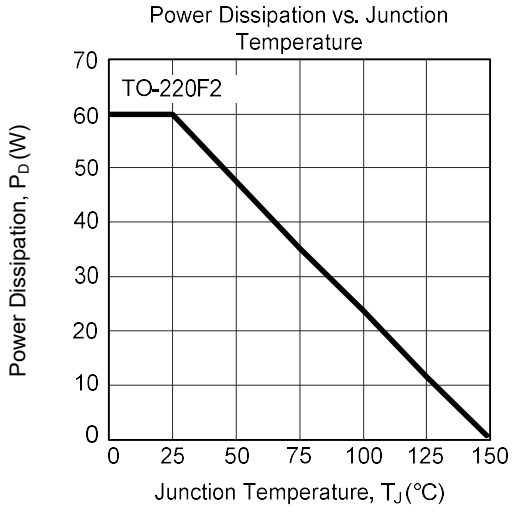
■ TYPICAL CHARACTERISTICS (Cont.)

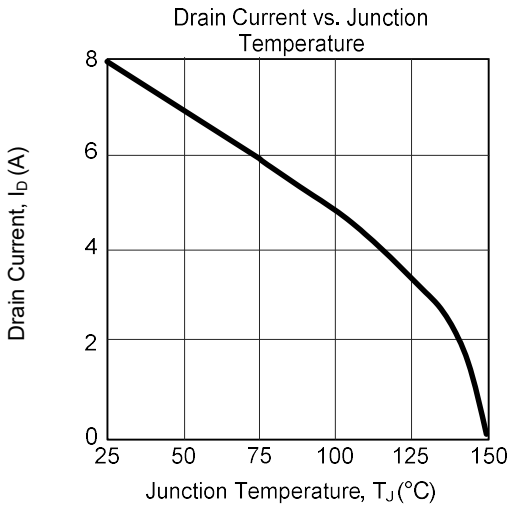




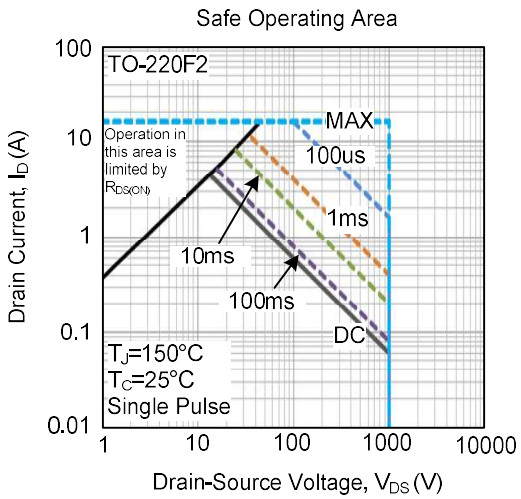








■ TYPICAL CHARACTERISTICS (Cont.)



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